

GSA1625

PNP SILICON TRANSISTOR

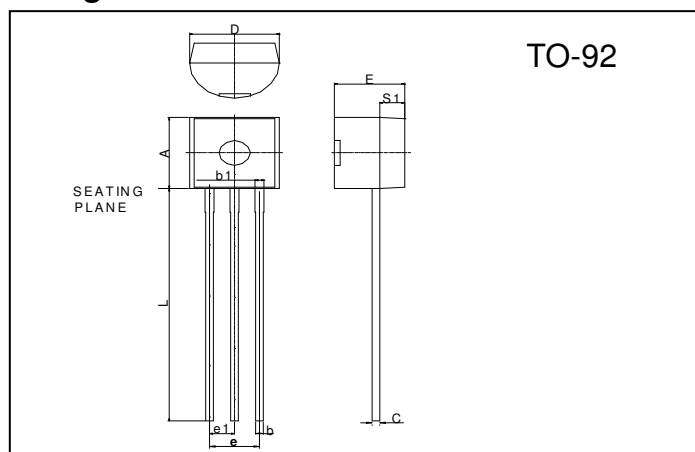
Description

The GSA1625 is designed for general purpose amplifier and high speed switching applications.

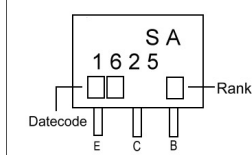
Features

- High Voltage
- High Speed Switching
- Low Collector Saturation Voltage

Package Dimensions



Marking :



| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|-------|
| | Min. | Max. | | Min. | Max. |
| A | 4.45 | 4.7 | D | 4.44 | 4.7 |
| S1 | 1.02 | - | E | 3.30 | 3.81 |
| b | 0.36 | 0.51 | L | 12.70 | - |
| b1 | 0.36 | 0.76 | e1 | 1.150 | 1.390 |
| C | 0.36 | 0.51 | e | 2.42 | 2.66 |

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Ratings | Unit |
|------------------------------|------------------|------------|------|
| Junction Temperature | T _j | +150 | °C |
| Storage Temperature | T _{stg} | -55 ~ +150 | °C |
| Collector to Base Voltage | VCBO | -400 | V |
| Collector to Emitter Voltage | VCEO | -400 | V |
| Emitter to Base Voltage | VEBO | -7 | V |
| Collector Current | I _C | -500 | mA |
| Collector Current(pulse)* | I _C | -1000 | mA |
| Total Power Dissipation | PD | 750 | mW |

*p_w ≤ 2ms, Duty Cycle ≤ 50%

Characteristics at Ta = 25°C

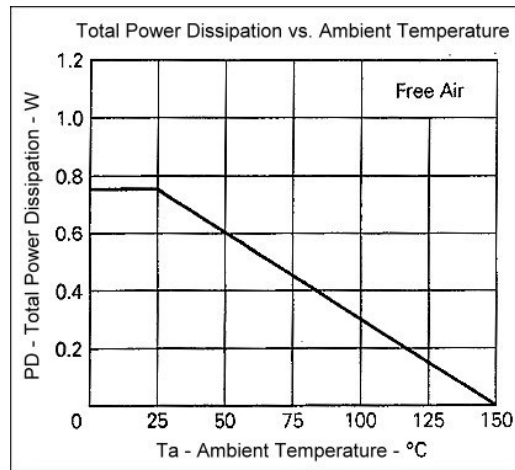
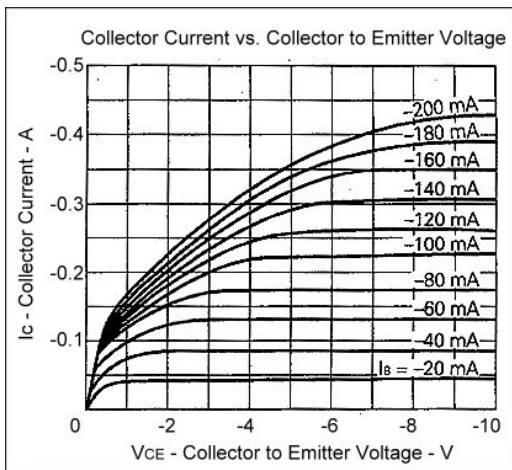
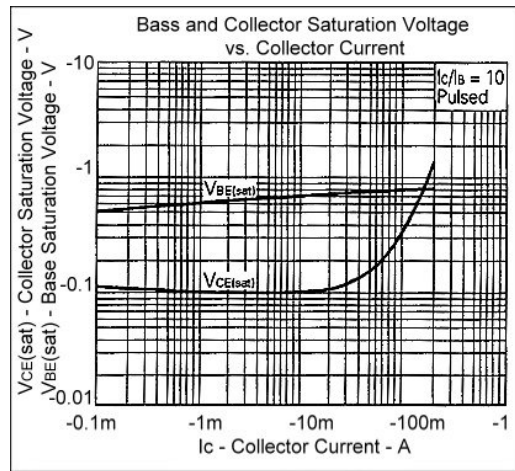
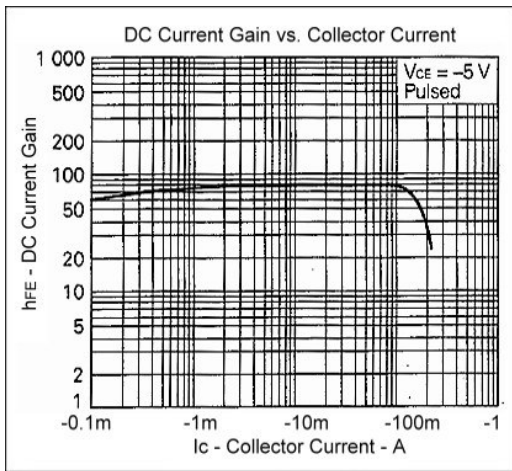
| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|-----------------|------|------|------|------|--|
| BVCBO | -400 | - | - | V | I _C = -100μA |
| BVCEO | -400 | - | - | V | I _C = -1mA |
| BVEBO | -7 | - | - | V | I _E = -100μA |
| ICBO | - | - | -10 | μA | V _{CB} = -400V, I _E = 0 |
| IEBO | - | - | -10 | μA | V _{EB} = -5V, I _C = 0 |
| *VCE(sat) | - | - | -0.5 | V | I _C = -100mA, I _B = -10mA |
| *VBE(sat) | - | - | -1.2 | V | I _C = -100mA, I _B = -10mA |
| *hFE | 40 | 80 | 200 | | V _{CE} = -5V, I _C = -50mA |
| f _T | 20 | 40 | - | MHz | V _{CE} = -10V, I _E = -10mA |
| C _{ob} | - | 17 | 20 | pF | V _{CB} = -10V, I _E = 0, f = 1MHz |

Classification Of hFE

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

| Rank | M | L | K |
|-------|---------|----------|----------|
| Range | 40 - 80 | 60 - 120 | 100 -200 |

Characteristics Curve



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165